

ELECTRONIC TUBE REFERENCE

GU73B

Power - Tetrode (NOT beam) (over 1000V 100W) electronic tube

CONSOLIDATED TECHNICAL DATA

1 SECTION
CONSTRUCTION
TETRODE

High-transconductance Soviet tetrode for single-sideband RF power amplification to approximately 250 MHz.

GENERAL CHARACTERISTICS

BASE DESIGNATION	—	BASE PINS	—
NOMINAL HEATER	27 V / —	PARALLEL HEATER	— / —
HEATING	Indirect	SERIES OPERATION	Not specified
CATHODE ARRANGEMENT	Separate cathodes	SECTION CONSTRUCTION	Similar

SECTION RATINGS

SECTION1 Tetrode	
TRANSCONDUCTANCE	0.065 S
AMPLIFICATION FACTOR	37
MAXIMUM PLATE VOLTAGE	3000 V
MAXIMUM SCREEN VOLTAGE	325 V
MAXIMUM PLATE DISSIPATION	2500 W
MAXIMUM SCREEN DISSIPATION	35 W
MAXIMUM GRID DISSIPATION	5 W
MAXIMUM CATHODE CURRENT	2.2 A
<i>Promoted-field audit performed from English ratings/characteristics; detailed electrical values retained in parameter table. REDO promoted-field audit completed from English Limit Operating Values / Electrical Parameters tables.</i>	

The GU-73B tetrode is used for single-sideband power amplification at frequencies up to 250 MHz. It has an indirectly heated oxide-coated cathode, metal-ceramic envelope, and forced-air cooling.

SOURCE OPERATING CONDITIONS

[SOURCE PDF](#)

1968 Electronintorg

Published test conditions and operating points. Values on this page are preserved as reported by this source.

1968 ELECTRONINTORG

Section 1 · Tetrode

OTHER		
PARAMETER	PUBLISHED VALUE	CONDITION / NOTE
power [1]	736 W	["eHepartopHbin TeTpog I'Y-736 npeaHasHayeH ana The I'Y-73b tetrode is used for single-sideband power
power [2]	73 W	["eHepartopHbin TeTpog I'Y-736 npeaHasHayeH ana The I'Y-73b tetrode is used for single-sideband power
YCUMEHUs1 MOLHOCTM OAHOMOMNOCHOrO CurHana Ha [1]	4	YCUMEHUs1 MOLHOCTM OAHOMOMNOCHOrO CurHana Ha 4a-amplification at frequencies up to 250 MHz.
YCUMEHUs1 MOLHOCTM OAHOMOMNOCHOrO CurHana Ha [2]	250	YCUMEHUs1 MOLHOCTM OAHOMOMNOCHOrO CurHana Ha 4a-amplification at frequencies up to 250 MHz.
anode; / - contact surfaces [1]	71	K — cathode; /71— heater; C1 — grid 1, C2 — grid 2; A — anode; / - contact surfaces
anode; / - contact surfaces [2]	1	K — cathode; /71— heater; C1 — grid 1, C2 — grid 2; A — anode; / - contact surfaces
anode; / - contact surfaces [3]	2	K — cathode; /71— heater; C1 — grid 1, C2 — grid 2; A — anode; / - contact surfaces
temperature, °C [1]	88 C	JIMHERHDBI® . . . o v it ettt e e 88 Lowest permissible ambient temperature, °C —60
temperature, °C [2]	-60 C	JIMHERHDBI® . . . o v it ettt e e 88 Lowest permissible ambient temperature, °C —60
voltage (ACorDC),V	27 V	Hanpsxenua Hakana (~wim =),B 27 Heater voltage (ACorDC),V
voltage, V [1]	250 V	e 250 Negative grid 1 bias voltage, V
voltage, V [2]	1 V	e 250 Negative grid 1 bias voltage, V

PARAMETER	PUBLISHED VALUE	CONDITION / NOTE
voltage, V,atmost	1840 V	CMELLEHUA CETKUNEPBOMA MuHyc 1840 Negative cutoff voltage, V,atmost
Mutual conductance, mA/V, atleast	-130 mA/V	TOK CeTKM BTOPOR, MA, —130 Mutual conductance, mA/V, atleast
grid2) [1]	65	KpyTusHa xapakTepycTuku, MA/B, He meHee 65 Gain coefficient (grid 1 grid2)
grid2) [2]	1	KpyTusHa xapakTepycTuku, MA/B, He meHee 65 Gain coefficient (grid 1 grid2)
Voltage level of combination frequencies of third	0 V	KoadhduumeHT ycuneHus ceTku nepei OTHOCUTENb- Voltage level of combination frequencies of third
grid [1]	37 kV	HOCETKMBTOPOM v.oiiiniinnnnnanennnnnnns 37 and fifth orders (at anode voltage 3 kV, grid 2
grid [2]	3 kV	HOCETKMBTOPOM v.oiiiniinnnnnanennnnnnns 37 and fifth orders (at anode voltage 3 kV, grid 2
grid [3]	2 kV	HOCETKMBTOPOM v.oiiiniinnnnnanennnnnnns 37 and fifth orders (at anode voltage 3 kV, grid 2
current [1]	300 mA	YpoBeHb HanpsHKeHui KOMOMHALUOHBBIX HacToT voltage 300 V, anode current 750 mA, grid 2 current
current [2]	750 mA	YpoBeHb HanpsHKeHui KOMOMHALUOHBBIX HacToT voltage 300 V, anode current 750 mA, grid 2 current
current [3]	2 mA	YpoBeHb HanpsHKeHui KOMOMHALUOHBBIX HacToT voltage 300 V, anode current 750 mA, grid 2 current
aHopaa [1]	3 s	aHopaa 3 kB, Hanpsixenuun ceTku BTopow 300 B, Warm up time,s,atmost
aHopaa [2]	300 s	aHopaa 3 kB, Hanpsixenuun ceTku BTopow 300 B, Warm up time,s,atmost
power under conditions of class AB [1]	750 W	Toke aHoaa 750 MA, Toke ceTku BTOn He 6onee Oscillatory power under conditions of class AB;
power under conditions of class AB [2]	6 W	Toke aHoaa 750 MA, Toke ceTku BTOn He 6onee Oscillatory power under conditions of class AB;

PARAMETER	PUBLISHED VALUE	CONDITION / NOTE
anode [1]	-30 kV	. —30 (atanode voltage 3 kV, grid 2 voltage 300 V, anode
anode [2]	3 kV	. —30 (atanode voltage 3 kV, grid 2 voltage 300 V, anode
anode [3]	2 kV	. —30 (atanode voltage 3 kV, grid 2 voltage 300 V, anode
anode [4]	300 kV	. —30 (atanode voltage 3 kV, grid 2 voltage 300 V, anode
current at most [1]	6 mA	Bpems roToBHOCTH, C, HE 6Onee 210 current 750 mA, grid 2 current at most 110 mA),
current at most [2]	210 mA	Bpems roToBHOCTH, C, HE 6Onee 210 current 750 mA, grid 2 current at most 110 mA),
current at most [3]	750 mA	Bpems roToBHOCTH, C, HE 6Onee 210 current 750 mA, grid 2 current at most 110 mA),
current at most [4]	2 mA	Bpems roToBHOCTH, C, HE 6Onee 210 current 750 mA, grid 2 current at most 110 mA),
current at most [5]	110 mA	Bpems roToBHOCTH, C, HE 6Onee 210 current 750 mA, grid 2 current at most 110 mA),
Interelectrode capacitance, pF	3 pF	(npv HanpsxxeHun aHoaa 3 KB, HaNpsiXKeHnn ceTku Interelectrode capacitance, pF:
input [1]	300	BTOpoK 300 B, Toke aHoga 750 MA, TOKe ceTku input ... 190
input [2]	750	BTOpoK 300 B, Toke aHoga 750 MA, TOKe ceTku input ... 190
input [3]	190	BTOpoK 300 B, Toke aHoga 750 MA, TOKe ceTku input ... 190
output [1]	6	B8TOpOW He 6onee 110 MA), kBT, He meHee 2,5 output
output [2]	110	B8TOpOW He 6onee 110 MA), kBT, He meHee 2,5 output
output [3]	25	B8TOpOW He 6onee 110 MA), kBT, He meHee 2,5 output
voltage, V [1]	325 V	CETKMN BTOPOM, MOCTOAHHOE 325 Negativegrid 1 voltage, V... 150

PARAMETER	PUBLISHED VALUE	CONDITION / NOTE
voltage, V [2]	1 V	CETKMN BTOPOМ, МОСТОАННОЕ 325 Negativegrid 1 voltage, V... 150
voltage, V [3]	150 V	CETKMN BTOPOМ, МОСТОАННОЕ 325 Negativegrid 1 voltage, V... 150
dissipation, kW	150 kW	оТрULaTeNibHOe CeTKU NEPBON 150 Anode dissipation, kW:
PaccenBaemas Han6onbLIAA MOWHOCTb single-sideband signal amplification	25	PaccenBaemas Han6onbLIAA MOWHOCTb single-sideband signal amplification 25
aHoAoM, kKBT: TV signal amplification	3.5	aHoAoM, kKBT: TV signal amplification 3.5
dissipation, W [1]	4 W	npyu yCuneHn 04HOMONOCHOTO Grid 2 dissipation, W
dissipation, W [2]	2 W	npyu yCuneHn 04HOMONOCHOTO Grid 2 dissipation, W
dissipation, W [1]	2 W	[= T 2T 2,5 Grid 1 dissipation, W
dissipation, W [2]	25 W	[= T 2T 2,5 Grid 1 dissipation, W
dissipation, W [3]	1 W	[= T 2T 2,5 Grid 1 dissipation, W
current (DC component), A	2.2 A	Npy YCUNEEHUM TEEHeBU3NOHHOIO Cathode current (DC component), A 2.2
current (instantaneous value), A	3.5 mA	CUTHAMA . . .ottt i e e e e 3.5 Anode current (instantaneous value), A
frequency, MHz	250 MHz	PaccenBaemas Han6onbLUasA MOLWHOCTD, BT: Operating frequency, MHz 250
anode, stem and seals, °C [1]	35 C	CETKOMBTOPOM oviiienieieie e 35 Temperature at anode, stem and seals, °C 200
anode, stem and seals, °C [2]	200 C	CETKOMBTOPOM oviiienieieie e 35 Temperature at anode, stem and seals, °C 200

TUBE TINKER

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